ABSTRACT OF THE DISCLOSURE

A semiconductor laser device has at least a first conductivity-type lower clad layers, a quantum well active layer, and a second conductivity-type upper clad layer, which are stacked on a first conductivity-type GaAs substrate. The quantum well active layer is composed of a barrier layer and a well layer which are alternately stacked and both made of an InGaAsP-based material. The quantum well active layer is grown while being doped with a second conductivity type of impurity so as for the semiconductor laser device to exhibits high reliability even at the time of high-power driving as well as long life.